



《风光欣》技术资料

HE882SC

NPN EPITAXIAL SILICON TRANSISTOR

2W OUTPUT AMPLIFIER OF PORTABLE

RADIOS IN CLASS

B PUSH-PULL OPERATION

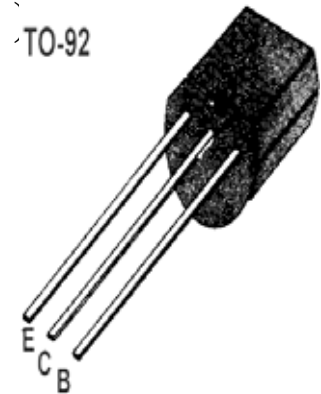
* Collector Current $I_{cm} = 1.5A$

* Collector Dissipation: $P_c = 1W$ ($T_A = 25$)

* Emitter-Collector-Base (ECB)

ABSOLUTE MAXIMUM RATINGS($T_A = 25$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter -Base Voltage	V_{EBO}	6	V
Collector Current	I_c	1.5	A
Collector Dissipation	P_c	1	W
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-65 ~150	



ELECTRICAL CHARACTERISTICS ($T_A = 25$)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	$I_c = 100 \mu A$ $I_E = 0$	40			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_c = 2mA$ $I_B = 0$	25			V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E = 100 \mu A$ $I_c = 0$	6			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = 35V$ $I_E = 0$			100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 6V$ $I_c = 0$			100	nA
DC Current Gain	H_{FE1}	$V_{CE} = 1V$ $I_c = 5mA$	45	170		
	H_{FE2}	$V_{CE} = 1V$ $I_c = 100mA$	85	160	300	
	H_{FE3}	$V_{CE} = 1V$ $I_c = 800mA$	40	80		
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = 800mA$ $I_B = 80mA$		0.28	0.5	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = 800mA$ $I_B = 80mA$		0.98	1.2	V
Base-Emitter Voltage	V_{BE}	$V_{CE} = 1V$ $I_c = 10mA$		0.66	1.0	V
Output Capacitance ($f = 1MHz$)	C_{OB}	$V_{CB} = 10V$ $I_E = 0$		10		pF
Current Gain-Bandwidth Product	f_T	$V_{CE} = 10V$ $I_c = 50mA$		100	200	MHz

HFE 2 : CLASSIFICATION

Classification	A	B	C
H_{FE}	100-200	160-320	200-400